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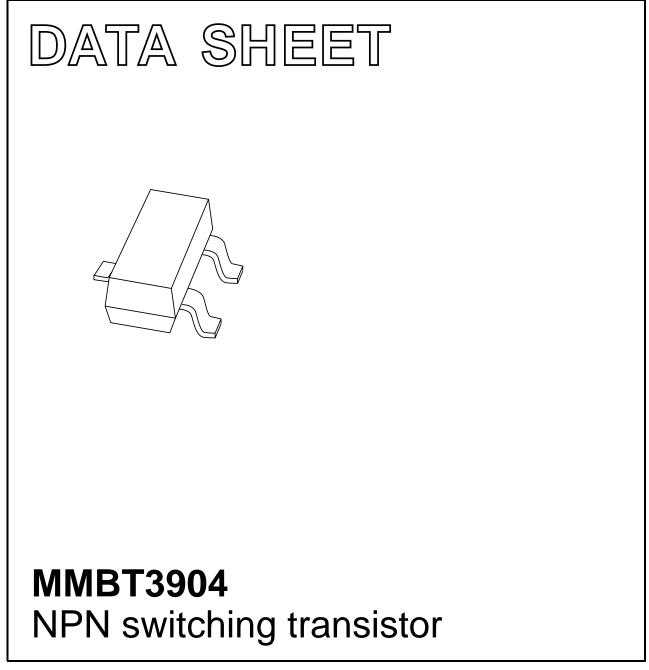
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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 2002 Oct 04 2004 Feb 03



MMBT3904

FEATURES

- Collector current capability I_C = 200 mA
- Collector-emitter voltage V_{CEO} = 40 V.

APPLICATIONS

• General switching and amplification.

DESCRIPTION

NPN switching transistor in a SOT23 plastic package. PNP complement: MMBT3906.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
MMBT3904	7A*

Note

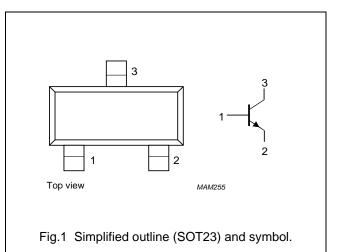
- 1. * = p: Made in Hong Kong.
 - * = t: Made in Malaysia.
 - * = W: Made in China.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage		V
I _C	collector current (DC)	200	mA

PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



ORDERING INFORMATION

		PACKAGE	
ITPE NUMBER	NAME	IE DESCRIPTION VERSI	
MMBT3904	_	plastic surface mounted package; 3 leads	SOT23

MMBT3904

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	60	V
V _{CEO}	collector-emitter voltage	open base	-	40	V
V _{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current (DC)		_	200	mA
I _{CM}	peak collector current		-	200	mA
I _{BM}	peak base current		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \text{ °C}; \text{ note } 1$	-	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

MMBT3904

CHARACTERISTICS

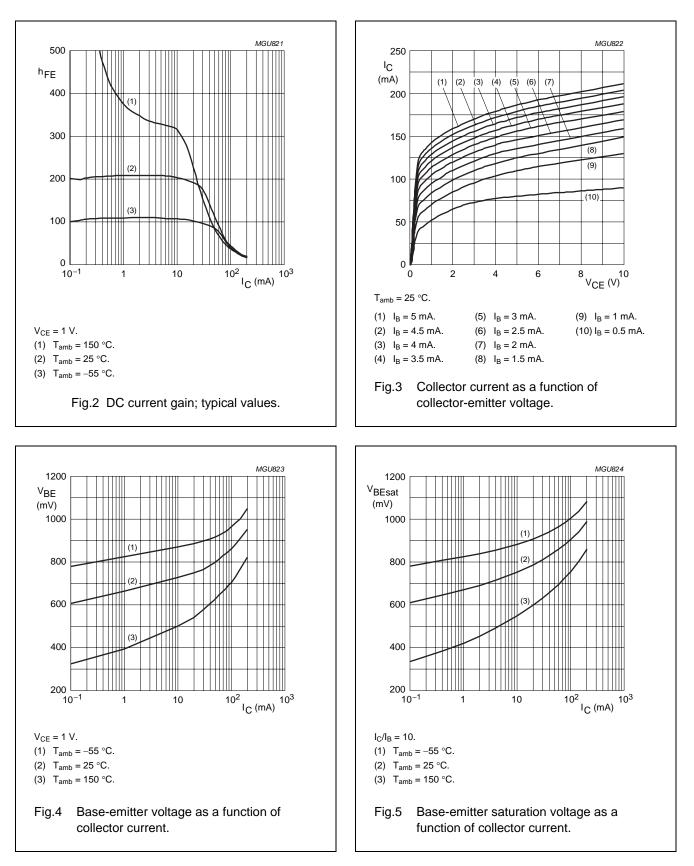
 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 30 V	_	50	nA
I _{EBO}	emitter cut-off current	$I_{\rm C} = 0; V_{\rm EB} = 6 \text{ V}$	_	50	nA
h _{FE}	DC current gain	V _{CE} = 1 V; see Fig.2; note 1			
		$I_{\rm C} = 0.1 {\rm mA}$	60	-	
		$I_{\rm C} = 1 \rm{mA}$	80	-	
		I _C = 10 mA	100	300	
		I _C = 50 mA	60	-	
		I _C = 100 mA	30	-	
V _{CEsat}	collector-emitter saturation	I _C = 10 mA; I _B = 1 mA	_	200	mV
	voltage	I _C = 50 mA; I _B = 5 mA	_	300	mV
V _{BEsat}	base-emitter saturation voltage	I _C = 10 mA; I _B = 1 mA	650	850	mV
		I _C = 50 mA; I _B = 5 mA	-	950	mV
C _c	collector capacitance	$I_{E} = I_{e} = 0; V_{CB} = 5 V; f = 1 MHz$	-	4	pF
C _e	emitter capacitance	$I_{C} = I_{c} = 0$; $V_{BE} = 500 \text{ mV}$; f = 1 MHz	-	8	pF
f _T	transition frequency	$I_{C} = 10 \text{ mA}; V_{CE} = 20 \text{ V};$ f = 100 MHz	300	-	MHz
F	noise figure	I_{C} = 100 μA; V _{CE} = 5 V; R _S = 1 kΩ; f = 10 Hz to 15.7 kHz	-	5	dB
Switching t	imes (between 10% and 90% lev	els); see Fig.3			
t _d	delay time	I _{Con} = 10 mA; I _{Bon} = 1 mA;	-	35	ns
t _r	rise time	I _{Boff} = -1 mA	_	35	ns
ts	storage time]	_	200	ns
t _f	fall time]	_	50	ns

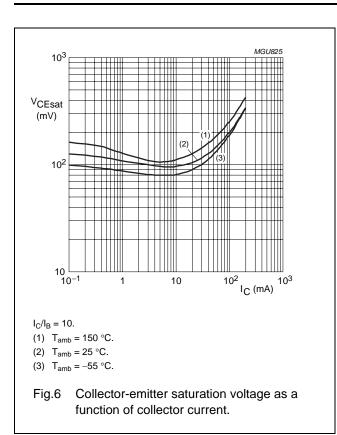
Note

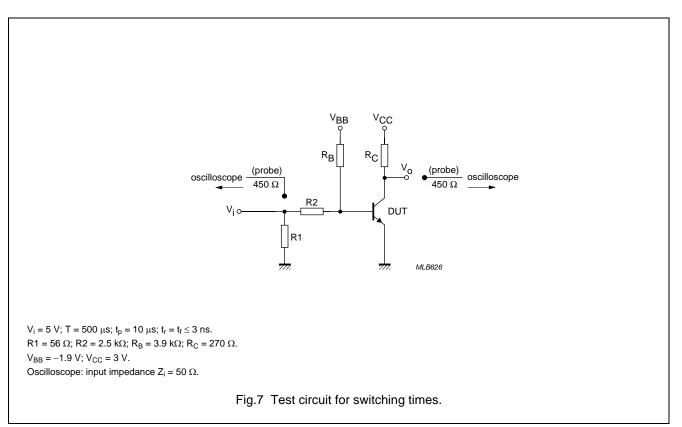
1. Pulse test: $t_p \leq 300~\mu\text{s};~\delta \leq 0.02.$

MMBT3904

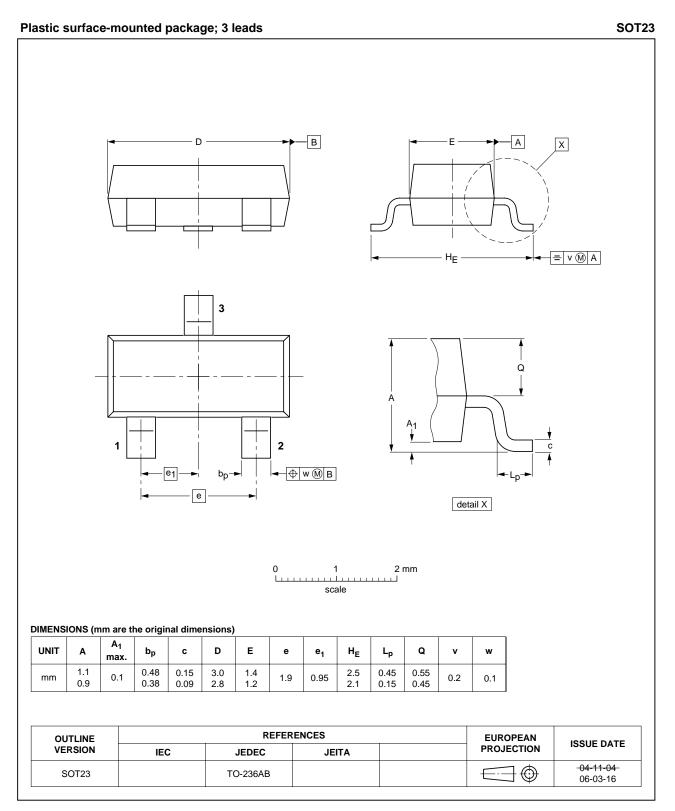


MMBT3904





PACKAGE OUTLINE



MMBT3904

MMBT3904

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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